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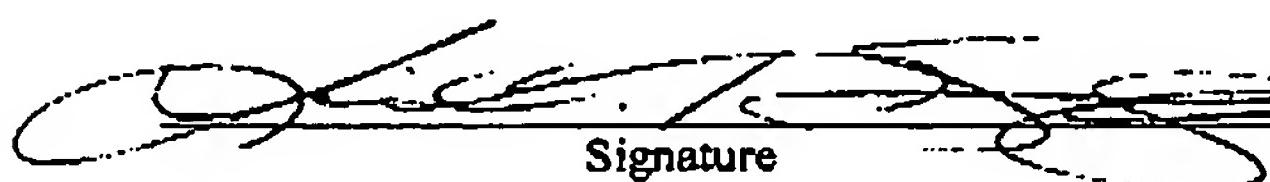
**Serial No.:** 10/709,776**Conf. No.:** 3775**Filing Date:** 05/27/2004**Art Unit:** 2811**Applicant:** William G. America**Examiner:** IM, Junghwa M.**Title:** SEMICONDUCTOR DEVICE  
FORMED BY IN-SITU MODIFICATION  
OF DIELECTRIC LAYER AND  
RELATED METHODS**Docket No.:** FIS920040083US1  
(IBM-0058)**COMMISSIONER FOR PATENTS****DESTINATION FACSIMILE NUMBER:** 571-273-8300

Transmitted herewith is: **Response to Restriction Requirement in 7 pages**  
in the above identified application.

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In Re Application of: William G. America      Conf. No.: 3775  
Serial No.: 10/709,776      Art Unit: 2811  
Filed: 5/27/2004      Dkt. #: FIS920040083US1 (IBMF-0058)  
Title: SEMICONDUCTOR DEVICE FORMED BY IN-SITU MODIFICATION OF DIELECTRIC LAYER AND RELATED METHODS      Examiner: IM, Junghwa M

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

## RESPONSE TO RESTRICTION REQUIREMENT

Sir:

## I. INTRODUCTORY COMMENTS

This paper is being filed in response to the Restriction Requirement dated September 22, 2005. Applicant hereby provisionally elects Group I, claims 1-7, with traverse.

10/709,776

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